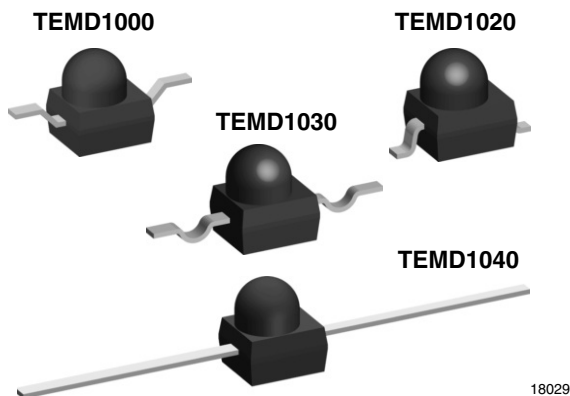


Silicon PIN Photodiode, RoHS Compliant



DESCRIPTION

TEMD1000 series are PIN photodiodes with high speed and high radiant sensitivity in black, surface mount plastic packages with lens and daylight blocking filter. Filter bandwidth is matched with 870 nm to 950 nm IR emitters.

FEATURES

- Package type: surface mount
- Package form: GW, RGW, yoke, axial
- Dimensions (L x W x H in mm): 2.5 x 2 x 2.7
- Radiant sensitive area (in mm²): 0.23
- High radiant sensitivity
- Daylight blocking filter matched with 870 nm to 950 nm emitters
- Fast response times
- Angle of half sensitivity: $\phi = \pm 15^\circ$
- Package matches with IR emitter series TSMF1000
- Floor life: 168 h, MSL 3, acc. J-STD-020
- Lead (Pb)-free component in accordance with RoHS 2002/95/EC and WEEE 2002/96/EC



RoHS
COMPLIANT

APPLICATIONS

- High speed detector for infrared radiation
- Infrared remote control and free air data transmissionsystems, e.g. in combination with TSFFxxxx series IR emitters

PRODUCT SUMMARY			
COMPONENT	I_{ra} (mA)	ϕ (deg)	$\lambda_{0.5}$ (nm)
TEMD1000	12	± 15	790 to 1050
TEMD1020	12	± 15	790 to 1050
TEMD1030	12	± 15	790 to 1050
TEMD1040	12	± 15	790 to 1050

Note

Test conditions see table "Basic Characteristics"

ORDERING INFORMATION			
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
TEMD1000	Tape and reel	MOQ: 1000 pcs, 1000 pcs/reel	Reverse gullwing
TEMD1020	Tape and reel	MOQ: 1000 pcs, 1000 pcs/reel	Gullwing
TEMD1030	Tape and reel	MOQ: 1000 pcs, 1000 pcs/reel	Yoke
TEMD1040	Bulk	MOQ: 1000 pcs, 1000 pcs/bulk	Axial leads

Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		V_R	60	V
Power dissipation	$T_{amb} \leq 25^\circ\text{C}$	P_V	75	mW
Junction temperature		T_j	100	$^\circ\text{C}$
Operating temperature range		T_{amb}	- 40 to + 85	$^\circ\text{C}$
Storage temperature range		T_{stg}	- 40 to + 100	$^\circ\text{C}$
Soldering temperature	$t \leq 5$ s	T_{sd}	< 260	$^\circ\text{C}$

Note

$T_{amb} = 25^\circ\text{C}$, unless otherwise specified



BASIC CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 50 \text{ mA}$	V_F		1	1.3	V
Breakdown voltage	$I_R = 100 \text{ }\mu\text{A}, E = 0$	$V_{(BR)}$	60			V
Reverse dark current	$V_R = 10 \text{ V}, E = 0$	I_{ro}		1	10	nA
Diode capacitance	$V_R = 5 \text{ V}, f = 1 \text{ MHz}, E = 0$	C_D		1.8		pF
Reverse light current	$E_e = 1 \text{ mW/cm}^2, \lambda = 870 \text{ nm}, V_R = 5 \text{ V}$	I_{ra}		10		μA
	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}, V_R = 5 \text{ V}$	I_{ra}	5	12		μA
Temperature coefficient of I_{ra}	$V_R = 5 \text{ V}, \lambda = 870 \text{ nm}$	$TK_{I_{ra}}$		0.2		%/K
Absolute spectral sensitivity	$V_R = 5 \text{ V}, \lambda = 870 \text{ nm}$	$s(\lambda)$		0.60		A/W
	$V_R = 5 \text{ V}, \lambda = 950 \text{ nm}$	$s(\lambda)$		0.55		A/W
Angle of half sensitivity		φ		± 15		deg
Wavelength of peak sensitivity		λ_p		940		nm
Range of spectral bandwidth		$\lambda_{0.5}$		790 to 1050		nm
Rise time	$V_R = 10 \text{ V}, R_L = 50 \text{ }\Omega, \lambda = 820 \text{ nm}$	t_r		4		ns
Fall time	$V_R = 10 \text{ V}, R_L = 50 \text{ }\Omega, \lambda = 820 \text{ nm}$	t_f		4		ns

Note

$T_{amb} = 25 \text{ }^\circ\text{C}$, unless otherwise specified

BASIC CHARACTERISTICS

$T_{amb} = 25 \text{ }^\circ\text{C}$, unless otherwise specified

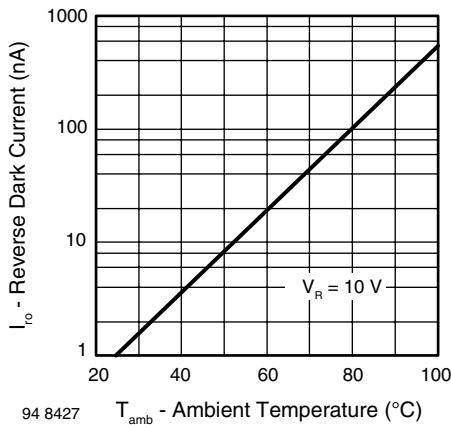


Fig. 1 - Reverse Dark Current vs. Ambient Temperature

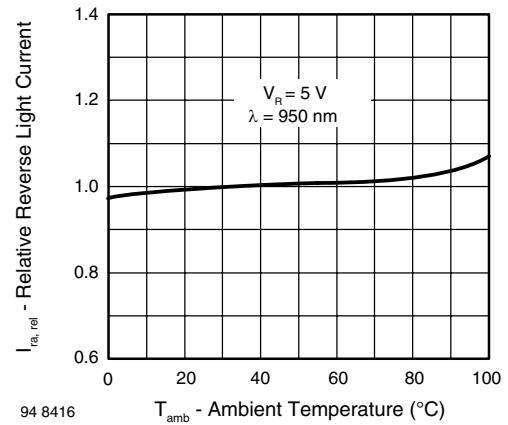


Fig. 2 - Relative Reverse Light Current vs. Ambient Temperature

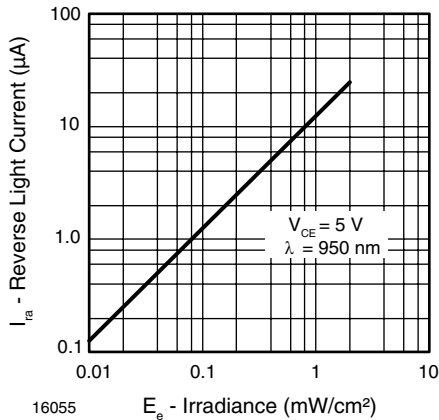


Fig. 3 - Reverse Light Current vs. Irradiance

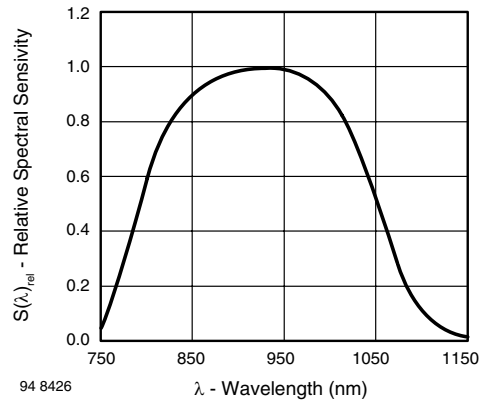


Fig. 5 - Relative Spectral Sensitivity vs. Wavelength

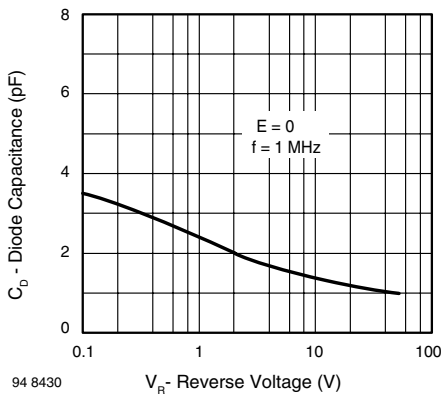


Fig. 4 - Diode Capacitance vs. Reverse Voltage

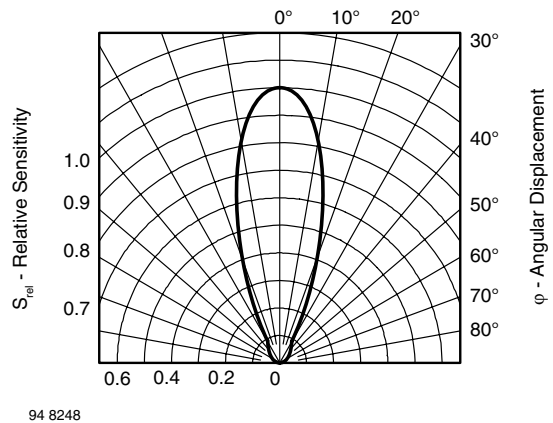


Fig. 6 - Relative Radiant Sensitivity vs. Angular Displacement

PRECAUTIONS FOR USE

1. Over-current-proof

Customer must apply resistors for protection, otherwise slight voltage shift will cause big current change (burn out will happen).

2. Storage

2.1 Storage temperature and rel. humidity conditions are: 5 °C to 35 °C, R.H. 60 %.

2.2 Floor life must not exceed 168 h, acc. to JEDEC level 3, J-STD-020.

Once the package is opened, the products should be used within a week. Otherwise, they should be kept in a damp proof box with desiccant. Considering tape life, we suggest to use products within one year from production date.

2.3 If opened more than one week in an atmosphere 5 °C to 35 °C, R.H. 60 %, devices should be treated at 60 °C ± 5 °C for 15 h.

2.4 If humidity indicator in the package shows pink color (normal blue), then devices should be treated with the same conditions as 2.3.

REFLOW SOLDER PROFILE

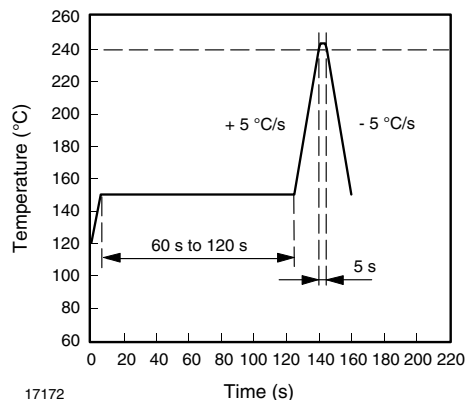


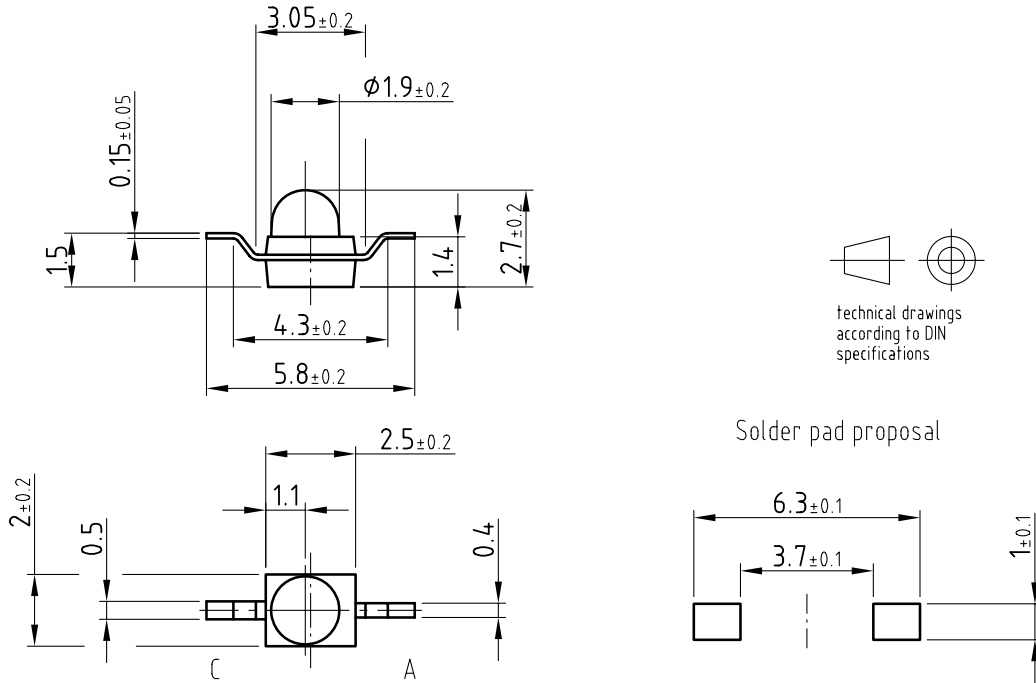
Fig. 7 - Lead Tin (SnPb) Reflow Solder Profile



TEMD1000, TEMD1020, TEMD1030, TEMD1040

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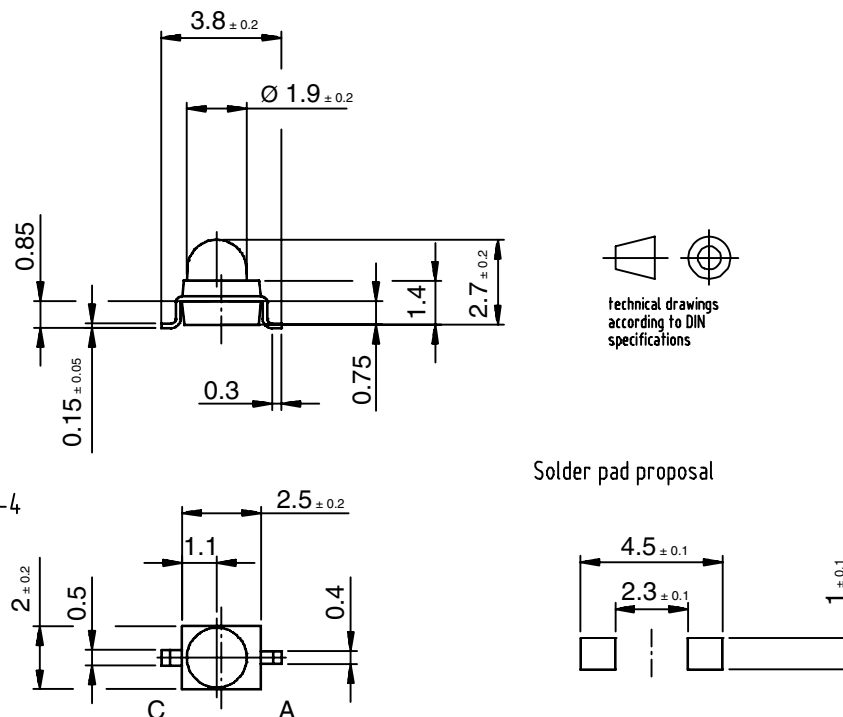
PACKAGE DIMENSIONS in millimeters: TEMD1000



Drawing-No.: 6.544-5326.02-4
Issue: 3; 02.04.03

16159

PACKAGE DIMENSIONS in millimeters: TEMD1020



Drawing-No.: 6.544-5325.02-4
Issue: 3; 02.04.03

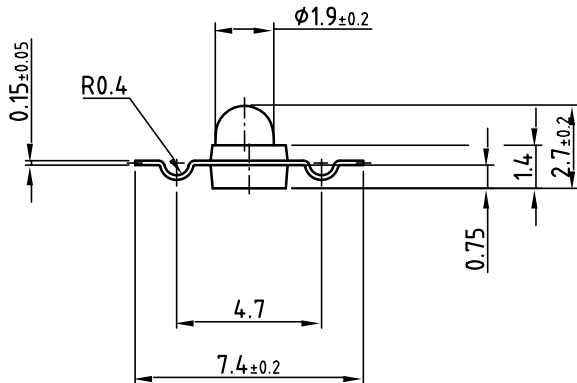
16160

TEMD1000, TEMD1020, TEMD1030, TEMD1040

Vishay Semiconductors Silicon PIN Photodiode, RoHS Compliant

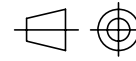


PACKAGE DIMENSIONS in millimeters: TEMD1030

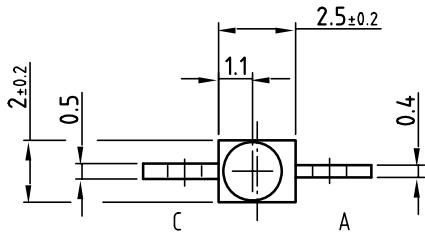


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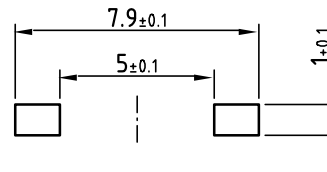
Issue: 4; 08.05.03



technical drawings
according to DIN
specifications

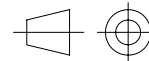
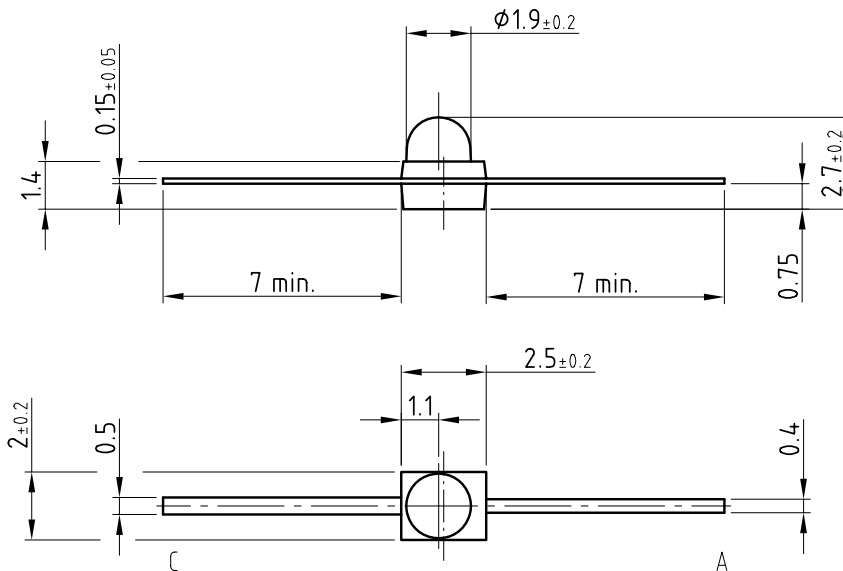


Solder pad proposal



16228

PACKAGE DIMENSIONS in millimeters: TEMD1040



technical drawings
according to DIN
specifications

Drawing-No.: 6.544-5339.02-4

Issue: 3; 02.04.03

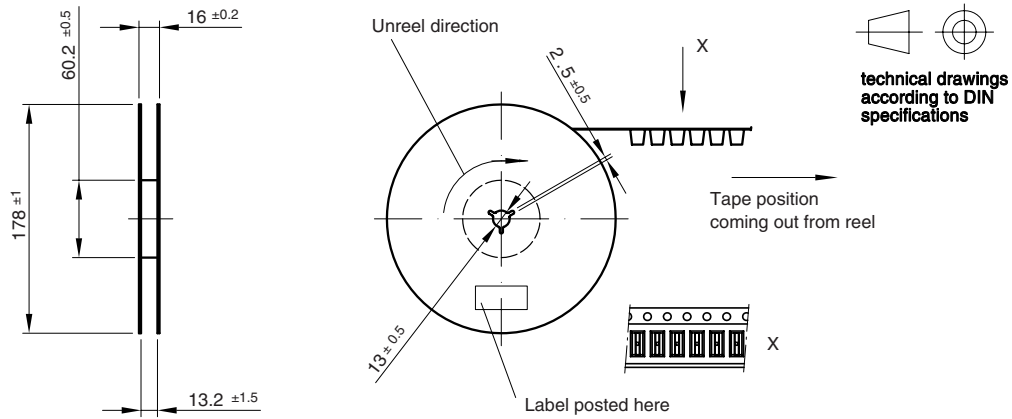
16760



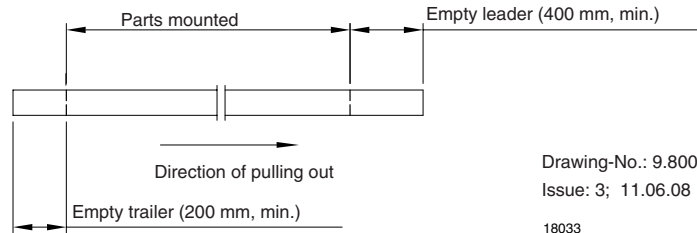
TEMD1000, TEMD1020, TEMD1030, TEMD1040

Silicon PIN Photodiode, RoHS Compliant Vishay Semiconductors

REEL DIMENSIONS in millimeters



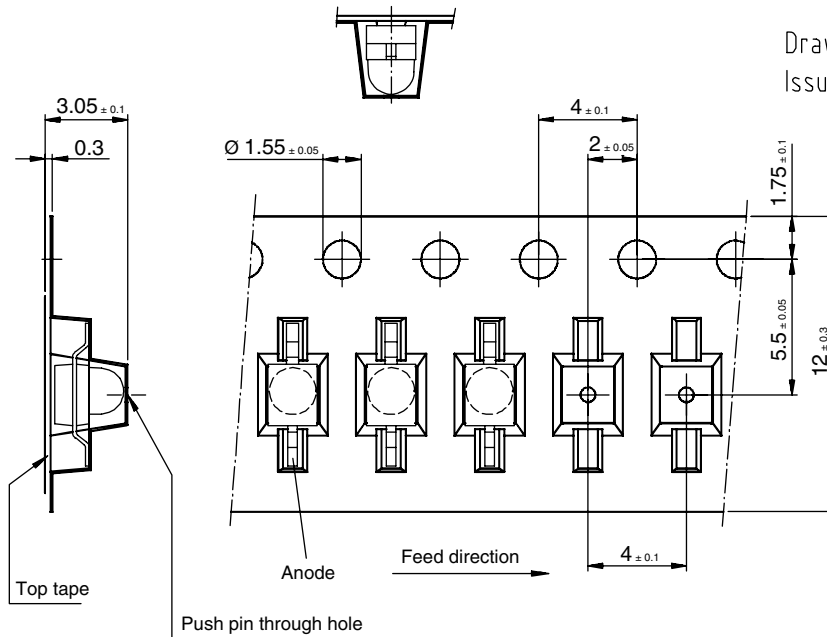
Leader and trailer tape:



Drawing-No.: 9.800-5080.01-4
Issue: 3; 11.06.08

18033

TAPING DIMENSIONS in millimeters: TEMD1000



Drawing-No.: 9.700-5268.01-4
Issue: 2; 22.11.02

Quantity per reel: 1000 pcs or 5000 pcs

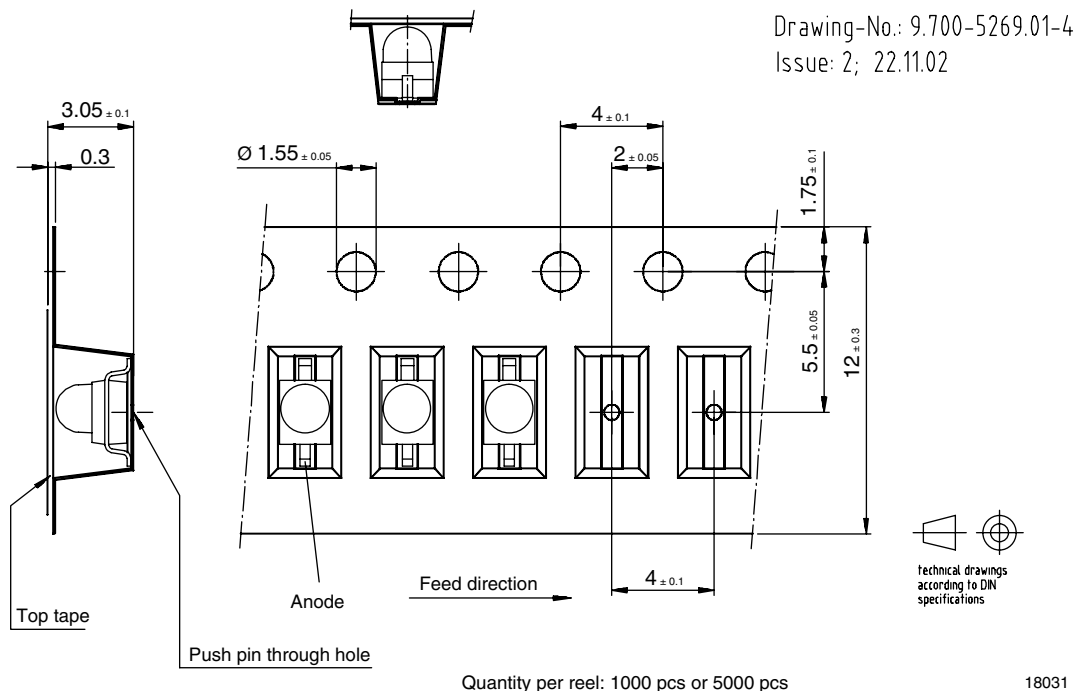
18030

TEMD1000, TEMD1020, TEMD1030, TEMD1040

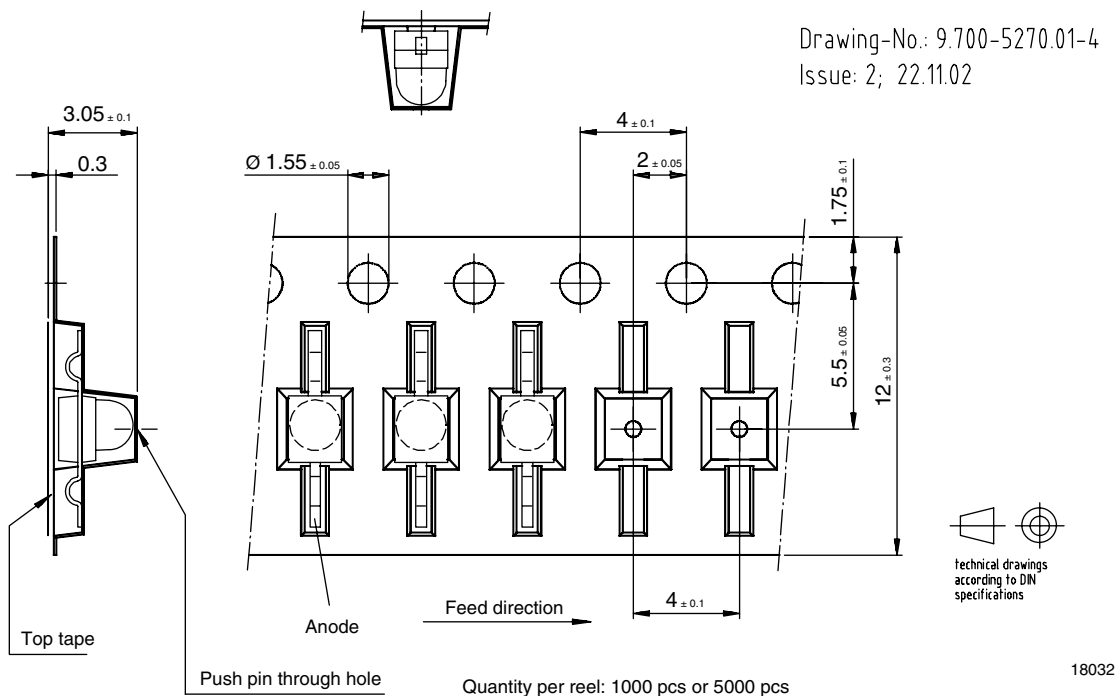
Vishay Semiconductors Silicon PIN Photodiode, RoHS Compliant



TAPING DIMENSIONS in millimeters: TEMD1020



TAPING DIMENSIONS in millimeters: TEMD1030





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